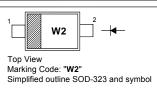
## SILICON EPITAXIAL PLANAR SWITCHING DIODE

#### **Features**

Fast switching diode

#### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



## Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)

Parameter		Symbol	Value	Unit
Reverse Voltage		$V_R$	75	V
Peak Reverse Voltage		$V_{RM}$	100	V
Forward Current (Continuous)		I <sub>F</sub>	250	mA
Non-Repetitive Peak Forward Current	t = 1 µs t = 1 ms t = 1 s	I <sub>FSM</sub>	2 1 0.5	A A A
Power Dissipation		P <sub>tot</sub>	200	mW
Junction Temperature		T <sub>j</sub>	150	°C
Storage Temperature Range		T <sub>stg</sub>	- 65 to + 150	°C

## Characteristics at T<sub>a</sub> = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 1$ mA at $I_F = 10$ mA at $I_F = 50$ mA at $I_F = 150$ mA	V <sub>F</sub>	0.715 0.855 1 1.25	V
Reverse Leakage Current at $V_R$ = 75 V at $V_R$ = 25 V, $T_J$ = 150 °C at $V_R$ = 75 V, $T_J$ = 150 °C	I <sub>R</sub>	1 30 50	μА
Diode Capacitance at $V_R = 0 V$ , $f = 1 MHz$	C <sub>tot</sub>	2	pF
Reverse Recovery Time at $I_F$ = 10 mA to $I_R$ = 10 mA, $I_R$ = 1 mA, $R_L$ = 100 $\Omega$	t <sub>rr</sub>	6	ns

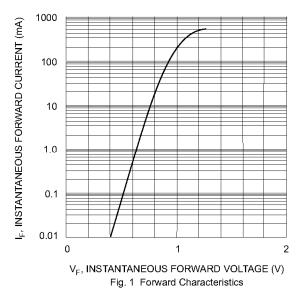


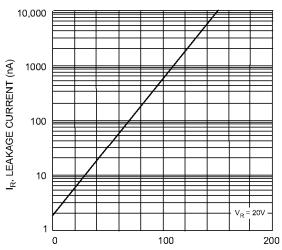












 $T_{j}$ , JUNCTION TEMPERATURE (°C) Fig. 2 Leakage Current vs Junction Temperature

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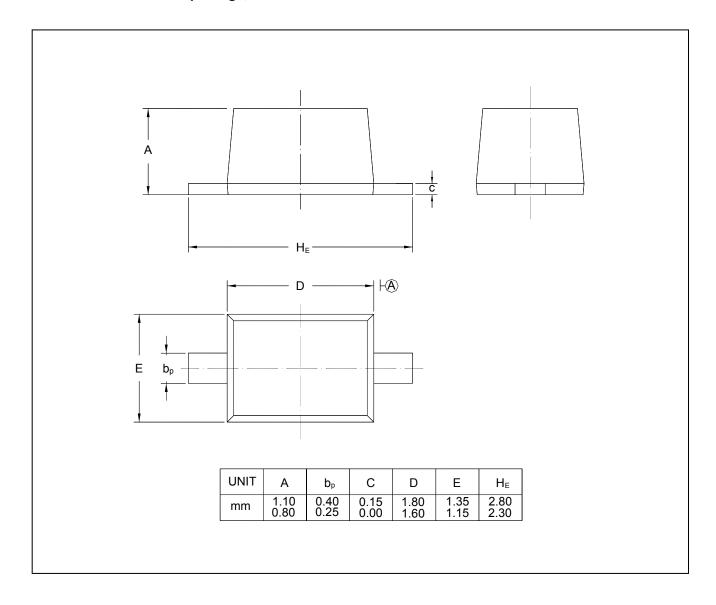




## **PACKAGE OUTLINE**

## Plastic surface mounted package; 2 leads

**SOD-323** 



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